



# ACE

## Engineering Academy



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### ESE- 2018 (Prelims) - Offline Test Series      Test-1

### ELECTRONICS & TELECOMMUNICATION ENGINEERING

#### SUBJECT: ANALOG ELECTRONICS, DIGITAL ELECTRONICS & MICROPROCESSORS – SOLUTIONS

##### 01. Ans: (c)

**Sol:** The given circuit is a wein-bridge oscillator. The condition for sustained oscillations (or) the minimum voltage gain required to maintain the oscillations in a wein-Bridge oscillator is

$$A_V = 1 + \frac{R_1}{R_2} + \frac{C_2}{C_1} \quad \dots\dots (1) \quad [\text{where } R_1 =$$

$2R$ ,  $R_2 = R$ ,  $C_1 = C$  and  $C_2 = 2C$  in the given circuit]

$$\Rightarrow 1 + \frac{R_f}{R_1} = 1 + \frac{2R}{R} + \frac{2C}{C} = 5 \quad \dots\dots (2)$$

$$\Rightarrow R_f/R_1 = 4 \quad \dots\dots (3)$$

$$\therefore R_f = 4R_1 \quad \dots\dots (4)$$

##### 02. Ans: (c)

**Sol:** Step(1):

when  $V_i = -2V$ ,  $V_A = -12V$

Step (2):

$$\because V_A = -12V, D \text{ is OFF} \Rightarrow V_0 = 0V$$

##### 03. Ans: (a)

**Sol:** Step (1) KVL for input loop

$$I_S = \frac{24V - 10V}{250\Omega} = 56mA$$

Step (2) KCL at (a)

$$I_L = I_S - I_Z$$

**Case (i):**  $I_{L_{max}} = I_S - I_{Z_{min}} = 53mA$

$$I_{L_{max}} = \frac{V_0}{R_{L_{min}}} = 53mA$$

$$\therefore R_{L_{min}} = \frac{10V}{53mA} = 188.679\Omega = 189\Omega$$

**Case (ii):**

$$I_{L_{min}} = \frac{V_0}{R_{L_{max}}} = I_S - I_{Z_{max}}$$

$$= 56mA - 50mA = 6mA$$

$$\therefore R_{L_{max}} = 10V / 6mA = 1.66k\Omega$$

##### 04. Ans: (d)

**Sol:** Step (1): KCL at collector node of  $Q_1$

$$I_{Ref} = I_{C_1} + I_{B_1} + I_{B_2}$$

$$= I_{C_1} + 2I_{B_2}$$

$$= I_{C_2} + \frac{2I_{C_2}}{\beta}$$

$$= I_{C_2} \left[ 1 + \frac{2}{\beta} \right]$$

$$\therefore \frac{I_{Ref}}{I_{C_2}} = \frac{I_{Ref}}{I_0} = 1 + \frac{2}{50} = 1.04$$



**05. Ans: (d)**

**Sol:** Given  $A = 1000$  and  $\beta = 0.0025$

$$20\% \text{ of } 1000 = 200$$

$$\Rightarrow A_{\text{New}} = 1000 - 200$$

$$= 800$$

$$\therefore A_{f_{\text{New}}} = \frac{A_{\text{New}}}{1 + A_{\text{New}}\beta}$$

$$= \frac{800}{1 + 800 \times 0.0025}$$

$$= 266.667$$

**06. Ans: (b)**

**Sol: Step (1):**

$$f_{L_f} = \frac{f_L}{1 + A\beta}$$

$$= \frac{2\text{kHz}}{1 + 1000 \times 0.01}$$

$$= 181.818\text{Hz}$$

**Step (2):**

$$f_{H_f} = f_H(1 + A\beta)$$

$$= 20\text{kHz} \times (1 + 1000 \times 0.01)$$

$$= 220\text{kHz}$$

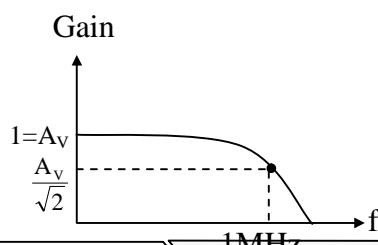
**07. Ans: (b)**

**Sol:** Bandwidth =  $f_H = 1\text{MHz}$

At  $f_H$ , Gain of the amplifier,  $A_V = \frac{1}{\sqrt{2}}$

$$\Rightarrow A_V = \frac{V_o}{V_i} = \frac{1}{\sqrt{2}} \text{ V}$$

$$V_o = \frac{V_i}{\sqrt{2}} = \frac{2}{\sqrt{2}} = \sqrt{2} \text{ V}$$



**08. Ans: (b)**

**Sol:** In negative feedback amplifiers

Voltage gain ↓

Bandwidth ↑

Noise ↓

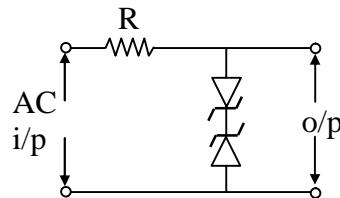
Distortion ↓

Amplitude fluctuations ↓

**09. Ans: (a)**

**10. Ans: (d)**

**Sol:**



**11. Ans: (a)**

$$\text{Sol: } V_H = 2V_{\text{sat}} \left( \frac{R_2}{R_1 + R_2} \right)$$

$$= 2 \times 10 \left( \frac{1}{1+9} \right)$$

$$= 2\text{V}$$

**12. Ans: (c)**

**Sol:**  $V_0 = \text{gain} \times \text{input voltage}$   
 $= A \times V_m \sin \omega t$  (i.e.,  $A \times V_m = V_x$ )

$$\frac{dV_0}{dt} = V_x \cos \omega t \times \omega$$

$$\text{SR} = \frac{dV_0}{dt} \Big|_{\text{max}} = V_x 2\pi f$$

$$\Rightarrow 100 \times 10^6 = V_x \times 2\pi \times 20 \times 10^6$$

$$V_x = \frac{100}{40\pi}$$

$$= \frac{5}{2\pi} \text{V}$$



13. Ans: (c)

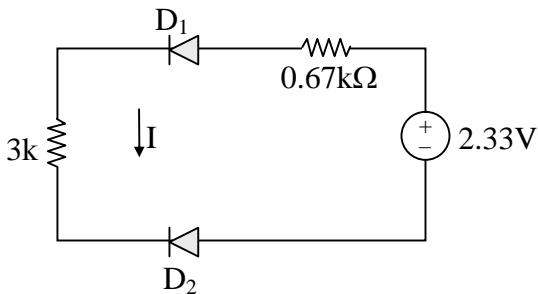
Sol:  $V_0 = -2(2) = -4V$

$$I_0 = -\frac{V_0}{2k} + \left( \frac{-V_0}{1k} \right)$$
$$= 2 \times 10^{-3} + 4 \times 10^{-3}$$
$$= 6mA$$

14. Ans: (a)

Sol: both the diodes are OFF

$$I=0$$



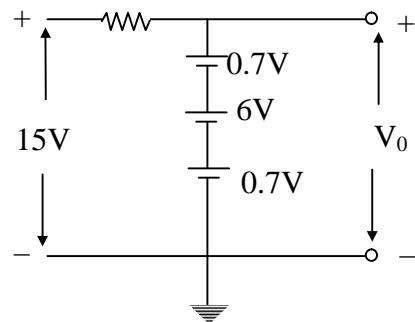
15. Ans: (c)

Sol: D → F B

$Z_1 \rightarrow$  operated in break down region

$Z_2 \rightarrow$  F B then

$$V_0 = 7.4V$$



# Pre GATE-2018

— COMPUTER BASED TEST —

Date of Exam : **20<sup>th</sup> Jan 2018**

Last Date To Apply : **05<sup>th</sup> Jan 2018**



16. Ans: (b)

17. Ans: (d)

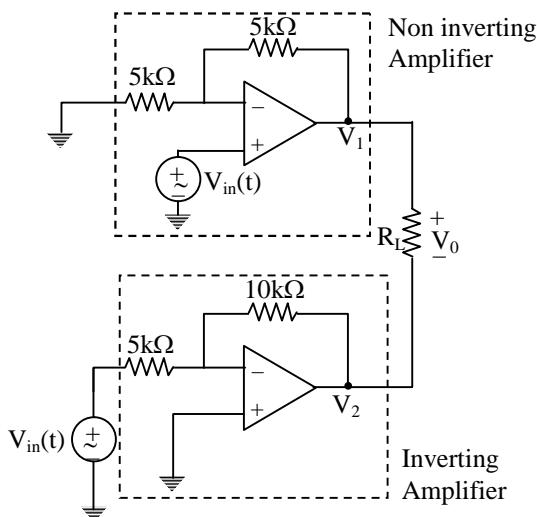
Sol:  $V_0 = \frac{R_2}{R_1} (V_1 - V_2)$

$$V_1 - V_2 = -2V$$

$$V_0 = 5(-2) \\ = -10V$$

18. Ans: (d)

Sol: In Ideal op-amp  $V_+ = V_-$  so equivalent circuit is



Output of the non-inverting amplifier is

$$V_1 = \left(1 + \frac{5k}{5k}\right) V_{in}(t) \\ = 2V_{in}(t)$$

Output of the inverting amplifier is

$$V_2 = \frac{-10k}{5k} V_{in}(t) \\ = -2V_{in}(t)$$

Therefore, the output voltage is

$$V_0 = V_1 - V_2 \\ = 2V_{in}(t) - (-2V_{in}(t)) \\ = 4V_{in}(t) \\ = 4 \times 3\sin\omega t \\ = 12\sin\omega t$$

19. Ans: (a)

Sol: For negative feedback, gain factor is reduced by  $(1+A\beta)$  for shunt-series,  $R_{in}$  is decreased by a factor of  $(1+A\beta)$ ,  $R_o$  is increased by a factor of  $(1+A\beta)$

20. Ans: (a)

Sol: Here the base emitter voltage is greater than 0.7 V and the base collector voltage is less than 0.7 V.

Hence base emitter junction is in forward bias and collector-base junction is in reverse bias.

∴ Transistor is in forward active region

21. Ans: (d)

Sol: Here  $I_{CBO}$  doubles for every  $10^0$  raise in temperature  $V_{BE}$  decreases at the rate of  $2.5 \text{ mV}/^\circ\text{C}$

22. Ans: (d)

Sol: P → RC coupled amplifier → Audio  
Q → Differential amplifier → DC and audio  
R → Cascode amplifier → Video  
S → Tuned amplifier → Narrow band

23. Ans: (d)

Sol: The oscillation frequency in crystal oscillator is determined by the crystal dimensions. This means that crystal oscillator frequency depends on all of the above parameters i.e. thickness of crystal, angle of cut and physical size of crystal

24. Ans: (a)

Sol: The transistor with comparatively small  $\beta$  is used in power amplifier because to handle large currents base of the transistor is made thicker. Hence  $\beta$  should be small



# ESE | GATE - 2019

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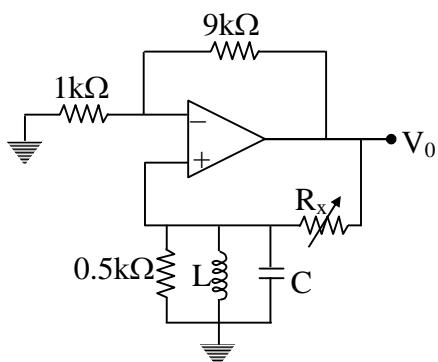
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25. Ans: (d)

Sol:



At sustained oscillations loop gain  $|A\beta| = 1$

At sustained oscillations (at resonance L-C circuit acts as open circuit).

$$\beta = \frac{V_f}{V_0} = \frac{0.5k}{R_x + 0.5k} \quad \& \quad A = \left[ 1 + \frac{9k}{1k} \right]$$

$$\text{As } |\beta A| = 1 \Rightarrow R_x = 4.5k\Omega$$

26. Ans: (c)

Sol: The upper cross-over voltage is

$$V_{TH} = + V_{sat} \left( \frac{R_1}{R_1 + R_2} \right) = +10 \left[ \frac{10k\Omega}{10k\Omega + 90k\Omega} \right] = +1 \text{ V}$$

The lower cross-over voltage is

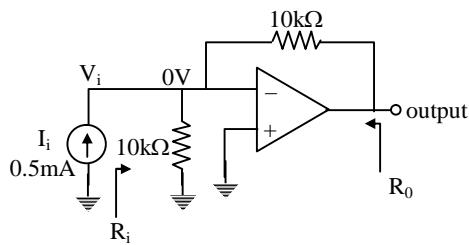
$$V_{TL} = - V_{sat} \left( \frac{R_1}{R_1 + R_2} \right) = -10 \left[ \frac{10k\Omega}{10k\Omega + 90k\Omega} \right] = -1 \text{ V}$$

The hysteresis width is therefore  $(V_{TH} - V_{TL}) = 1 - (-1) = 2 \text{ V}$



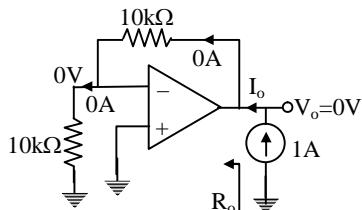
27. Ans: (b)

Sol:



$$\text{Input resistance } (R_i) = \frac{V_i}{I_i} = \frac{0}{0.5m} = 0\Omega$$

For output resistance, input current 0.5mA is open circuited & connected 1A current source at output as show in below figure.



$$\Rightarrow \text{Output resistance } (R_o) = \frac{V_o}{I_o} = \frac{0}{1} = 0\Omega$$

28. Ans (c)

Sol: The Common Emitter current gain – bandwidth product of a transistor ( $f_T$ ) is defined as the frequency at which Beta of the transistor falls to unity

$$\text{Unity gain frequency } (f_T) = \frac{g_m}{2\pi(C_\pi + C_\mu)}$$

29. Ans: (a)

Sol: The bias stability of an Emitter-Bias Amplifier circuit improves by decreasing the value of  $R_B$  and increasing the value of  $R_E$ .

30. Ans: (d)

Sol:  $A_V = -g_m r_{01}$

$$= \frac{-I_{EE}/2}{V_t} \left[ \frac{V_A}{I_{EE}/2} \right]$$

$$= \frac{-V_A}{V_t} = \frac{-5}{0.026} = -192.31$$

31. Ans: (d)

Sol: In current series feedback output current is proportional to input voltage. Hence it is Transconductance amplifier.

32. Ans: (a)

33. Ans: (b)

34. Ans: (a)

Sol: In PLA  $\Rightarrow$  both “AND” and “OR” programmable  
 (iii) represents Fan out  
 (iv) The basic circuit a TTL represents is a NAND gate.

35. Ans: (b)

Sol:  $2^N \geq (\text{no of digits in sequence}) + 1$

N: number of flip-flops

$$2^N \geq 5 + 1$$

$$N = 3$$

So number of flip-flops = 3

36. Ans: (d)

Sol: All three are major applications

37. Ans: (a)

Sol: Using SOP form

$$\begin{aligned} Y &= \overline{A} \overline{B} (1) + \overline{A} B (1) + A \overline{B} + AB(B) \\ &= \overline{A} \overline{B} + \overline{A} B + A \overline{B} + AB \\ &= 1 \end{aligned}$$

Using POS form

$$\begin{aligned} Y &= (A + B + 1)(A + \overline{B} + 1)(\overline{A} + B + A)(\overline{A} + \overline{B} + B) \\ &= (1)(1)(1)(1) \\ &= 1 \end{aligned}$$



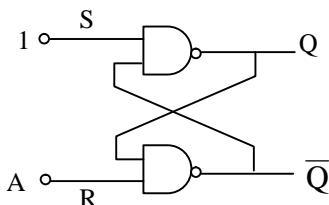
38. Ans: (b)

$$\begin{aligned} \text{Sol: } x \oplus y &= \overline{x \odot y} \\ &= \overline{xy + \bar{x}\bar{y}} \\ &= \overline{0 + \bar{x}\bar{y}} \\ &= \overline{\bar{x}\bar{y}} \\ &= \bar{x}y \\ &= x+y \end{aligned}$$

OR gate

39. Ans: (d)

Sol: Though oscillations are there when switch is closed, we need to get constant waveform without oscillations (bounce)



Fix 'S' at logic '1', connect A to 'R' input of SR NAND latch

When  $A = 0 \Rightarrow R = 0 \Rightarrow \bar{Q} = 1 \Rightarrow Q = 0$

Now, even if  $A = 1$  (due to bounce)  
i.e.  $R = 1$

$\Rightarrow Q$  remains in previous state i.e., ( $Q = 0$ )

40. Ans: (a)

Sol:

$D_7$	$D_6$	$D_5$	$D_4$	$D_3$	$D_2$	$D_1$	$D_0$	X	Y	Z
0	0	0	0	0	0	0	1	0	0	0
0	0	0	0	0	0	1	0	0	0	1
0	0	0	0	0	1	0	0	0	1	0
0	0	0	0	1	0	0	0	0	1	1
0	0	0	1	0	0	0	0	1	0	0
0	0	1	0	0	0	0	0	1	0	1
0	1	0	0	0	0	0	0	1	1	0
1	0	0	0	0	0	0	0	1	1	1

$$X = D_4 + D_5 + D_6 + D_7$$

$$Y = D_2 + D_3 + D_6 + D_7$$

$$Z = D_1 + D_3 + D_5 + D_7$$

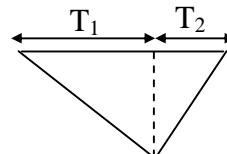
41. Ans: (c)

Sol:  $(V_{in}) \cdot T_1 = (V_{ref}) \cdot T_2$

$$(1) (10 \times 20 \text{ msec}) = (2) T_2$$

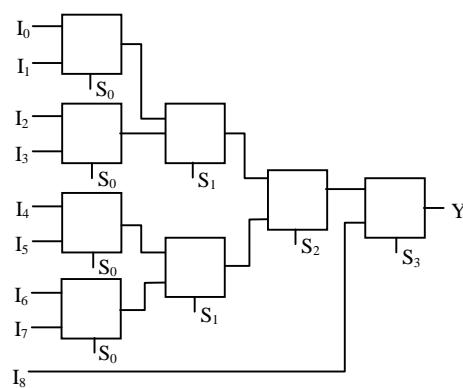
$$T_2 = 100 \text{ msec}$$

$$\text{Total time} = T_1 + T_2 = 0.3 \text{ sec}$$



42. Ans: (c)

Sol: Implementation is as shown



43. Ans: (d)

$$\begin{aligned} \text{Sol: } X &= (P + Q + R)(\bar{P} + Q + \bar{R}) \\ &= PQ + P\bar{R} + \bar{P}Q + Q + QR + \bar{P}R + QR \\ &= Q(1 + P + \bar{P} + \bar{R} + R) + \bar{P}R + \bar{P}R \\ &= (P \oplus R) + Q \end{aligned}$$

44. Ans: (d)

45. Ans: (b)

$$\text{Sol: } \sqrt{3r^2 + r + 1} = r + 4$$

$$3r^2 + r + 1 = r^2 + 8r + 16$$

$$2r^2 - 7r - 15 = 0$$

$$2r^2 - 10r + 3r - 15 = 0$$

$$2r(r-5) + 3(r-5) = 0$$

$$(r-5)(2r+3) = 0$$

$$r = 5 \quad \text{or} \quad -1.5 \text{ (invalid)}$$

46. Ans: (b)

Sol: XOR operation gives output HIGH, when odd no. of input variables are HIGH. So, by



looking at the truth table. Option 1 and 3 are correct.

AB \ CD	00	01	11	10
00		1		1
01	1		1	
11		1		1
10	1		1	

**47. Ans: (a)**

**Sol:** Cache memory is a very high speed memory that is placed between the CPU and main memory. The cache stores the copies of the data from frequently used main memory locations

**Memory Interleaving:** main memory is divided into two or more sections. The CPU can access alternate sections immediately without waiting for memory to catch up (through wait states)

**GATE - 2018**  
**ONLINE TEST SERIES**  
**No. of Tests : 62**

All tests will be available till  
12<sup>th</sup> February 2018

**ESE - 2018 PRELIMS**  
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**No. of Tests : 44**

All tests will be available till  
07<sup>th</sup> January 2018

**ISRO - 2017**  
**ONLINE TEST SERIES**  
**No. of Tests : 15**

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25<sup>th</sup> December 2017

**★ HIGHLIGHTS ★**

- Detailed solutions are available.
- **All India rank** will be given for each test.
- Comparison with all India toppers of **ACE** students.



48. Ans: (c)

49. Ans: (c)

Sol: CMOS inverter is formed by the series connection of one n-channel and one p-channel MOS transistor

Whereas transmission gate is formed by the parallel connection of one p-channel and one n-channel MOS transistors

50. Ans: (b)

51. Ans: (a)

52. Ans: (b)

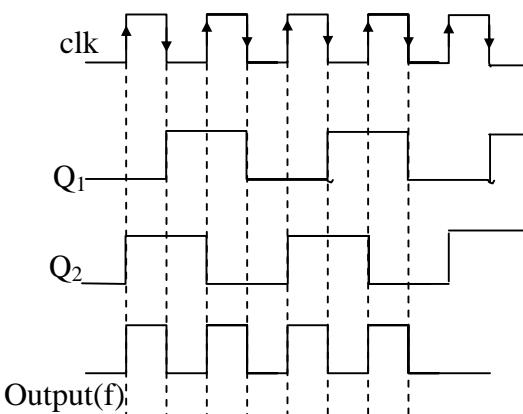
Sol:

Clkpulse	Input	Q <sub>3</sub>	Q <sub>2</sub>	Q <sub>1</sub>
0		0	0	0
1	1	1	0	0
2	1	1	1	0
3	1	1	1	1
4	0	0	1	1
5	0	0	0	1
6	0	0	0	0

$\overline{Q}_1$  is fed as input in Johnson counter

53. Ans: (a)

Sol:



Output is same as clk

$\therefore$  The frequency of output is 50MHz

54. Ans: (a)

Sol:  $f_{\max} = 10\text{MHz} = \frac{1}{n t_{pdff}}$

$$10\text{MHz} = \frac{1}{n(12.5)}$$

$$n = \frac{1}{10\text{MHz} \times 12.5\text{ns}}$$

$$n = 8$$

$$\text{Modulus} = 2^8 = 256$$

55. Ans: (c)

Sol: The time taken for SIPO is  $T_1 = NT$

The time taken for SISO is

$$T_2 = (2N-1) T$$

$$T_2 - T_1 = (N-1) T$$

56. Ans: (c)

Sol: (a) & (b) are operations performed when RESET IN is made low

(c) is performed when RESET out is made high

(d) is performed during DMA data transfer

57. Ans: (b)

58. Ans: (a)

Sol: A 01

A 00, (Cy = 0, AC = 0)

Loop: A FF (bit carry flag is not affected)

JC loop is failed

Hence HLT is executed

59. Ans: (b)

Sol: ADD M  $\Rightarrow$  All flags affected

CMP M  $\Rightarrow$  All flags affected

DCR M  $\Rightarrow$  Except carry flag, all flags are affected

RAL  $\Rightarrow$  Only carry flag is affected

60. Ans: (b)



**61. Ans: (d)**

**Sol:** 0100 MVI A, 00H  
0102 LXI H, 0105H  
0105 OUT 00H  
0106 INR A  
0107 PCHL  
0108 HLT

A $\leftarrow$ 00	HL $\leftarrow$ 0105	01 $\rightarrow$ [00]	02 $\rightarrow$ [00]
HL $\leftarrow$ 0105	A $\rightarrow$ [00]	A $\leftarrow$ 02	A $\leftarrow$ 03
A $\rightarrow$ [00]	A $\leftarrow$ 02	A $\leftarrow$ 03	
A $\leftarrow$ 01	PC $\leftarrow$ 0105		$\leftarrow$ 0105
PC $\leftarrow$ 0105			
Infinite loop			

**62. Ans: (a)**

**Sol:** Given  $A + A\bar{B} + A\bar{B}C$   
 $= A(1 + \bar{B} + \bar{B}C) = A$

No NAND gate is required to implement the expression

**63. Ans: (c)**

**Sol:**  $F_1, F_2 = \Sigma m(4,6) + d(1,2,3,7)$

$\downarrow$   
(common  
minterms of  $F_1, F_2$ )

$$F_1 + F_2 = \Sigma m(0,1,2,3,4,6) + d(7)$$

$$(F_1 \cdot F_2) + (F_1 + F_2) = \Sigma m(0,1,2,3,4,6) + d(7)$$

$$d \cdot 0 = 0$$

$$d \cdot d = d$$

$$1 \cdot d = d$$

$$d + d = d$$

$$1 + d = 1$$

$$0 + d = d$$

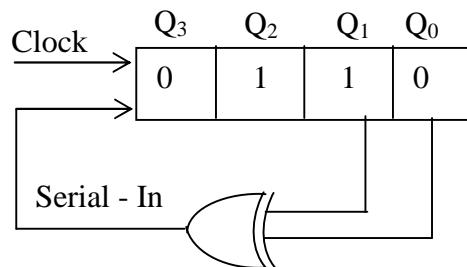
**64. Ans: (d)**

**Sol:**

$F = \overline{AC} + A\overline{C} = A \oplus C$

**65. Ans: (c)**

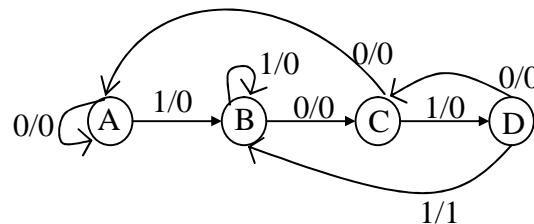
**Sol:**



CLK	Serial In	Q <sub>3</sub>	Q <sub>2</sub>	Q <sub>1</sub>	Q <sub>0</sub>
		0	1	1	0
1	1	1	0	1	1
2	0	0	1	0	1
3	1	1	0	1	0

**66. Ans: (c)**

**Sol:** The state diagram to detect the sequence 1011 is given below.



Total no. of states are = 4.

$\therefore$  2 flip flops are required to detect the sequence 1011

**67. Ans: (c)**

**Sol:** Given,  $N = 8E$

$$V_{ref} = 10$$

$$V_o = \frac{V_{ref}}{2^N} \sum_{j=0}^{N-1} 2^j b_j$$

$$\text{Digital input} = 10100001$$

$$\therefore V_o = \frac{10}{2^8} [1 + 2^5 + 2^7]$$

$$V_o = 6.289 \text{ V}$$



**68. Ans: (c)**

**Sol:** TRAP has both edge & level sensitive.

**69. Ans: (d)**

**Sol:** The given memory chip size = 8K  
 $= 8 \times 1024 = 2^3 \times 2^{10} = 2^{13}$   
13 address lines.

**70. Ans: (c)**

**Sol:** Vector Address for RST  $4.5 = 4.5 \times 8$   
 $= 36$   
 $= 0024 \text{ H}$

**71. Ans: (b)**

**Sol:** The gain of the CE amplifier at low frequencies depend on the coupling, bypass and blocking capacitors and independent of interelectrode capacitances. ( $C_{\pi}, C_{\mu}$ )

**72. Ans: (a)**

**73. Ans: (b)**

**Sol:** Both A & R are individually true, but R is not the correct explanation

**74. Ans: (a)**

**75. Ans: (d)**

## **GATE TOPPERS**

<b>1</b> EC PRAMOD	<b>1</b> ME SUDHEER	<b>1</b> ME HASAN ASIF	<b>1</b> EE SHIVAM SINGH	<b>1</b> CE MAEOLI PARASH	<b>1</b> CS DEVAL N PATEL	<b>1</b> IN NAVEEN	<b>2</b> EC SREE KALYANI
<b>2</b> CE PUNEET KHANNA	<b>2</b> IN RAHUL MISHRA	<b>2</b> IN SHUBHAM BANSAL	<b>2</b> PI GAURAV BHADAVALI	<b>3</b> EC KARUN	<b>3</b> EE RAVI TEJA	<b>3</b> ME PRADIP BOBADE	<b>3</b> CS RAVI SHANKAR
<b>3</b> CE ANKUR THIMATHI	<b>4</b> EC SONU SHARMA	<b>4</b> EE SARFRAJ HAWAZ	<b>4</b> CE CHIRAG MITTAL	<b>4</b> ME GAUSH ALAM	<b>4</b> IN MOINTI	<b>4</b> PI Sanjana Singh Adikari	<b>5</b> IN VRAMESH SHAH
<b>5</b> PI ANKIT TIWARI	<b>6</b> EC LIGITA SAI GUPTA	<b>6</b> CS MEGHASHAYAM	<b>6</b> EE RADHESHAR EDDOY	<b>6</b> IN RAMESH KAMBLE	<b>6</b> PI PINKAL KUMAR RANA	<b>7</b> IN PANKAJ MISHRA	<b>8</b> ME DIVYANSHU JHA
<b>8</b> PI Monu Bhangu	<b>9</b> EC Anmol Upadhyay	<b>9</b> CS Nitin Kumar Singh	<b>9</b> ME Dhruv Kumar Jain	<b>10</b> EC AMIT BAWAT	<b>10</b> ME Aman Gupta	<b>10</b> EE Suraj DASH	<b>10</b> IN Pranav Mehta

## **ESE TOPPERS**

<b>(CE)</b>		<b>(E&amp;T)</b>		<b>(EE)</b>		<b>(ME)</b>	
<b>1</b> CE NAMIT JAIN	<b>2</b> CE PRAVIND SINGH	<b>2</b> E&T SUDESH KHANNA	<b>3</b> E&T SIVAKRISHNAN	<b>2</b> EE PRIYANTI KUMARI	<b>3</b> EE RAMA CHANDRA GEORGE	<b>3</b> ME SAURABH	<b>4</b> ME AMIT KUMAR RAJ
<b>3</b> CE ANKIT	<b>6</b> CE KIRAN BHAKCH	<b>5</b> E&T AMIT GAUTAM	<b>6</b> E&T SUBHRANGINI MISHRA	<b>4</b> EE HARSHIT KUMAR SINGH	<b>5</b> EE NIRGIL KUMAR	<b>6</b> ME ANKAN GUPTA	<b>7</b> ME DHRIWJHA
<b>8</b> CE ADITYA SINGH	<b>9</b> CE HIMANSHU GAUTAM	<b>7</b> E&T DAKSHIKA PRASANNA KUMARI	<b>8</b> E&T DEEPAKI GOVAL	<b>6</b> EE DUSHYANT SINGH	<b>8</b> EE APORVAA GUPTA	<b>9</b> ME ACHARAJ GUPTA	
<b>10</b> CE AYUSH DUBEY	<b>7</b> IN TOP 10 RANKS	<b>9</b> E&T ABHIShek PRATAP SINGH	<b>10</b> E&T UMESH	<b>9</b> EE KIRAN BABU KONERU			<b>5</b> IN TOP 10 RANKS
		<b>8</b> IN TOP 10 RANKS		<b>7</b> IN TOP 10 RANKS			<b>27</b> Ranks in Top 10 in ESE-2017
				and many more...			



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